

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
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Hiroki et al.)
)
Serial No.:)
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Filed: Herewith)
)
For: Semiconductor Display Device And Method)
Of Driving A Semiconductor Display Device)
)
Examiner:)
)
Art Unit:)

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Date of Deposit July 13, 2001

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Name Ruben M. Gomez
(typed or printed)

Signature Ruben M. Gomez

Commissioner for Patents
Washington D.C. 20231

PRELIMINARY AMENDMENT A

Prior to examination, please enter the following amendment in the above-identified application:

IN THE CLAIMS:

Please amend the claims as follows:

16 (Amended) A semiconductor display device according to claim 1, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

17 (Amended). A computer using the semiconductor display device according to any one of claims 1 to 16 and 25 to 38.

18 (Amended). A video camera using the semiconductor display device according to any one of claims 1 to 16 and 25 to 38.

19 (Amended). A DVD player using the semiconductor display device according to any one of claims 1 to 16 and 25 to 38.

Please add the following new claims:

25 (New). A semiconductor display device according to claim 2, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

26 (New). A semiconductor display device according to claim 3, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

27 (New). A semiconductor display device according to claim 4, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

28 (New). A semiconductor display device according to claim 5, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

29 (New). A semiconductor display device according to claim 6, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

30 (New). A semiconductor display device according to claim 7, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

31 (New). A semiconductor display device according to claim 8, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

32 (New). A semiconductor display device according to claim 9, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

33 (New). A semiconductor display device according to claim 10, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

34 (New). A semiconductor display device according to claim 11, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

35 (New). A semiconductor display device according to claim 12, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

36 (New). A semiconductor display device according to claim 13, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

37 (New). A semiconductor display device according to claim 14, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

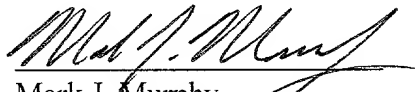
38 (New). A semiconductor display device according to claim 15, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon. --

REMARKS

This amendment is being submitted to remove the improper dependency upon multi-dependent claims. It is believed that no new matter is being added. Accordingly, it is requested that this amendment be entered.

If any additional fee is due for this amendment, please charge our deposit account 50/1039.

Respectfully submitted,


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Marked up copy of claims as amended:

16 (Amended) A semiconductor display device according to [any one of claims 1 to 15] claim 1, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

17 (Amended). A computer using the semiconductor display device according to any one of claims 1 to 16 and 25 to 38.

18 (Amended). A video camera using the semiconductor display device according to any one of claims 1 to 16 and 25 to 38.

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37 (New). A semiconductor display device according to claim 14, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon.

38 (New). A semiconductor display device according to claim 15, wherein the switching element is: a transistor formed using single crystal silicon; a thin film transistor formed using polycrystalline silicon; or a thin film transistor formed using amorphous silicon. --